

Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	-30	V
Gate-Source Voltage		V_{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = -10V	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-8.7 -7.0	А
Continuous Drain Current (Note 7) V _{GS} = -10V	$T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$	I _D	-30 -25	А
Continuous Drain Current (Note 6) V _{GS} = -5V	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-7.2 -5.8	А
Continuous Drain Current (Note 7) V _{GS} = -5V	$T_C = +25$ °C $T_C = +70$ °C	I _D	-30 -24	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	-80	Α
Maximum Continuous Body Diode Forward Current (Note 6)		Is	-3.6	Α
Avalanche Current (Note 7) L=0.3mH		I _{AS}	-17.5	Α
Avalanche Energy (Note 7) L=0.3mH		Eas	64	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	6	137	°C/W
	t<10s	$R_{\theta JA}$	65	°C/W
Total Power Dissipation (Note 6)		P_{D}	2.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	2	55	°C/W
Thermal Resistance, Junction to Ambient (Note o)	t<10s	$R_{\theta JA}$	26	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	3.5	°C/W
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

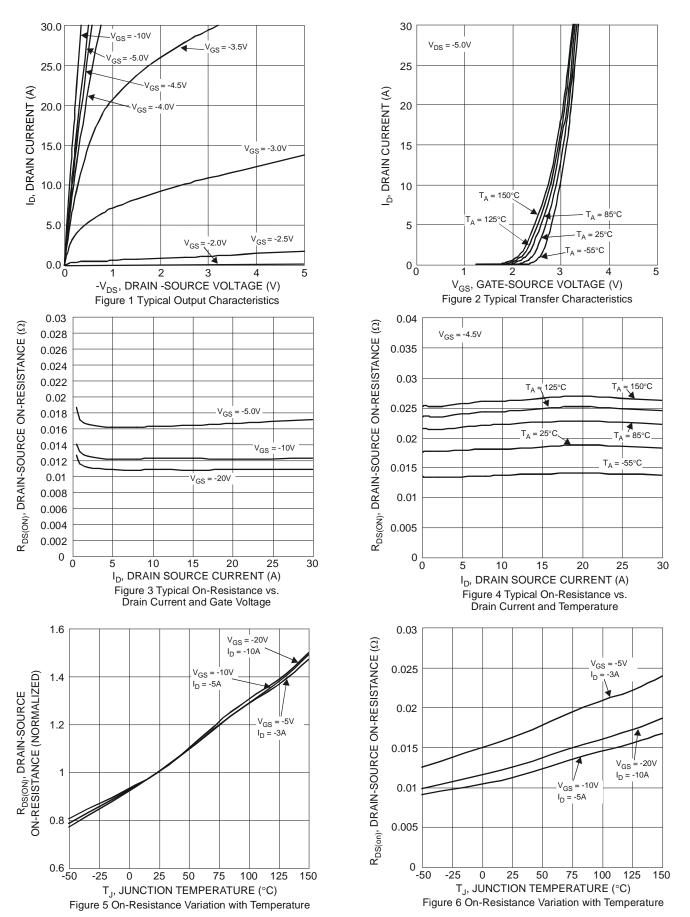
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	-	-	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	-1.0	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	-2.0	-2.5	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		-	13	20	mΩ	$V_{GS} = -10V, I_D = -8A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	-	18.4	29	mΩ	$V_{GS} = -5V, I_{D} = -5A$	
Diode Forward Voltage	V _{SD}	-	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)						•	
Input Capacitance	C _{iss}	-	1931	-	pF	15)/)/	
Output Capacitance	Coss	-	226	-	pF	$V_{DS} = -15V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	-	168	-	pF	1 = 1.0lvii iz	
Gate Resistance	Rg	-	10.9	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge V _{GS} = -5V	Qg	-	8.8	-	nC		
Total Gate Charge V _{GS} = -10V	Qg	-	16.5	-	nC	15)/ 15)/ 1 100	
Gate-Source Charge	Q_{gs}	-	2.6	-	nC	$V_{DS} = -15V, I_D = -10A$	
Gate-Drain Charge	Q _{gd}	-	3.6	-	nC	7	
Turn-On Delay Time	t _{D(ON)}	-	8.2	-	ns		
Turn-On Rise Time	t _R	-	14	-	ns	$V_{GS} = -10V, V_{DD} = -15V,$	
Turn-Off Delay Time	t _{D(OFF)}	-	65	-	ns	$R_{GEN} = 3\Omega$, $I_D = -10A$	
Turn-Off Fall Time	t _F	-	31.6	-	ns	1	
Reverse Recovery Time	t _{RR}	-	9.3	-	ns	I _F = -8A, di/dt = 500A/μs	
Reverse Recovery Charge	Q_{RR}	-	12.2	-	nC		

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.







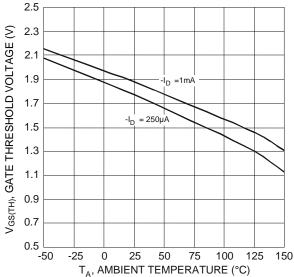


Figure 7 Gate Threshold Variation vs. Ambient Temperature

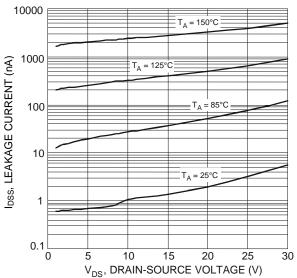
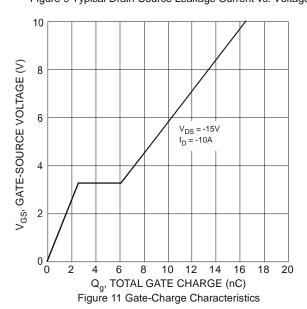
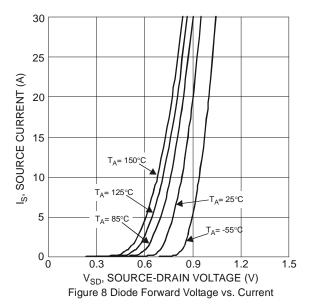
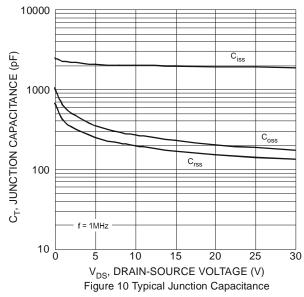
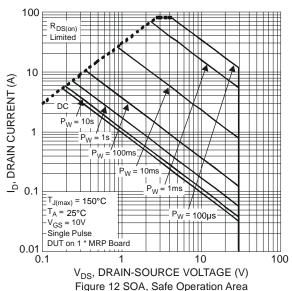


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

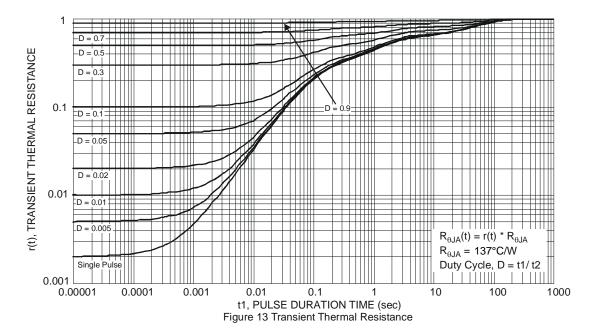










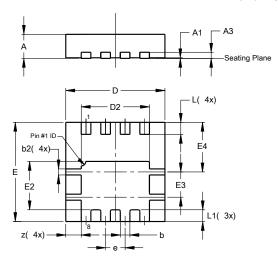




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

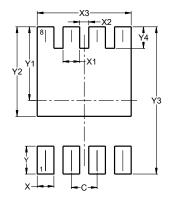


PowerDI3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A3	_	_	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	-	_	0.65			
L	0.35	0.45	0.40			
L1	_	_	0.39			
Z	_	_	0.515			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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